Micro Commercial Components
20736 Marilla Street Chatsworth
CA 91311
Phone: (818) 701-4933
Fax: (818) 701-4939

2SC1623

NPN Silicon Epitaxial Transistors

Features

- High DC Current Gain: h_{FE}=200 TYP.(V_{CE}=6.0V, I_C=1.0mA)
- High voltage: V_{CEO}=50V

Maximum Ratings

Symbol	Rating	Rating	Unit
V_{CEO}	Collector-Emitter Voltage	50	V
V_{CBO}	Collector-Base Voltage	60	V
V_{EBO}	Emitter-Base Voltage	5.0	V
I_C	Collector Current	100	mA
P_C	Collector power dissipation	200	mW
T_J	Junction Temperature	-55 to +150	^{0}C
T_{STG}	Storage Temperature	-55 to +150	^{0}C

Electrical Characteristics @ 25^{0}C Unless Otherwise Specified

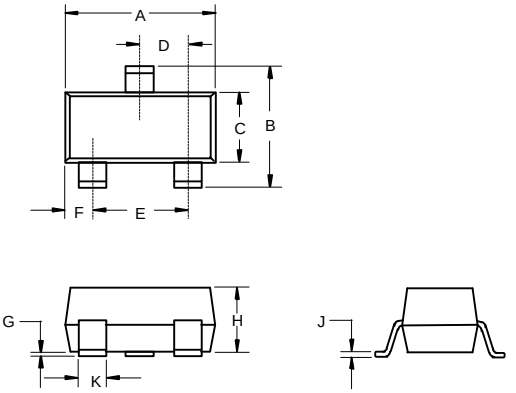
Symbol	Parameter	Min	Typ	Max	Units
OFF CHARACTERISTICS					
I_{CBO}	Collector Cutoff Current (V_{CB}=60Vdc,I_E=0)	---	---	0.1	uAdc
I_{EBO}	Emitter Cutoff Current (V_{EB}=5.0Vdc, I_C=0)	---	---	0.1	uAdc
ON CHARACTERISTICS					
h_F	DC Current Gain* (I_C=1.0mAdc, V_{CE}=6.0Vdc)	90	200	600	---
$V_{CE(sat)}$	Collector Saturation Voltage* (I_C=100mAdc, I_B=10mAdc)	---	0.15	0.3	Vdc
$V_{BE(SAT)}$	Base Saturation Voltage* (I_C=100mAdc,I_B=10mAdc)	---	0.86	1.0	Vdc
V_{BE}	Base Emitter Voltage* (V_{CE}=6.0Vdc, I_C=1.0mAdc)	0.55	0.62	0.65	Vdc
C_{ob}	Collector Capacitance (V_{CB}=6.0Vdc, I_E=0, f=1.0MHz)	---	3.0	---	pF
f_T	Gain Bandwidth product (V_{CE}=6.0Vdc, I_E=10mAdc)	---	250	---	MHz

h_{FE} CLASSIFICATION

Marking	L4	L5	L6	L7
h_{FE}	90-180	135-270	200-400	300-600

* Pulse Test PW<350us, duty cycle<2%

SOT-23



DIMENSIONS					
	INCHES		MM		
DIM	MIN	MAX	MIN	MAX	NOTE
A	.110	.120	2.80	3.04	
B	.083	.098	2.10	2.64	
C	.047	.055	1.20	1.40	
D	.035	.041	.89	1.03	
E	.070	.081	1.78	2.05	
F	.018	.024	.45	.60	
G	.0005	.0039	.013	.100	
H	.035	.044	.89	1.12	
J	.003	.007	.085	.180	
K	.015	.020	.37	.51	

Suggested Solder Pad Layout